# 74LVC1G66

Bilateral switch

Rev. 8 — 2 December 2011

**Product data sheet** 

#### 1. **General description**

The 74LVC1G66 provides one single pole, single-throw analog switch function. It has two input/output terminals (Y and Z) and an active HIGH enable input pin (E). When E is LOW, the analog switch is turned off.

Schmitt-trigger action at the enable input makes the circuit tolerant of slower input rise and fall times across the entire  $V_{CC}$  range from 1.65 V to 5.5 V.

#### 2. **Features and benefits**

- Wide supply voltage range from 1.65 V to 5.5 V
- Very low ON resistance:
  - 7.5  $\Omega$  (typical) at  $V_{CC} = 2.7 \text{ V}$
  - 6.5  $\Omega$  (typical) at  $V_{CC} = 3.3 \text{ V}$
  - 6  $\Omega$  (typical) at  $V_{CC} = 5 \text{ V}$
- Switch current capability of 32 mA
- High noise immunity
- CMOS low power consumption
- TTL interface compatibility at 3.3 V
- Latch-up performance meets requirements of JESD78 Class I
- ESD protection:
  - ♦ HBM JESD22-A114F exceeds 2000 V
  - ♦ MM JESD22-A115-A exceeds 200 V
- Enable input accepts voltages up to 5.5 V
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C

#### **Ordering information** 3.

Table 1. **Ordering information** 

Type number	Package			
	Temperature range	Name	Description	Version
74LVC1G66GW	–40 °C to +125 °C	TSSOP5	plastic thin shrink small outline package; 5 leads; body width 1.25 mm	SOT353-1
74LVC1G66GV	–40 °C to +125 °C	SC-74A	plastic surface-mounted package; 5 leads	SOT753
74LVC1G66GM	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body $1 \times 1.45 \times 0.5$ mm	SOT886



**Bilateral switch** 

 Table 1.
 Ordering information ...continued

Type number	Package						
	Temperature range	Name	Description	Version			
74LVC1G66GF	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 $\times$ 1 $\times$ 0.5 mm	SOT891			
74LVC1G66GN	–40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body $0.9 \times 1.0 \times 0.35$ mm	SOT1115			
74LVC1G66GS	–40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body $1.0 \times 1.0 \times 0.35$ mm	SOT1202			

### 4. Marking

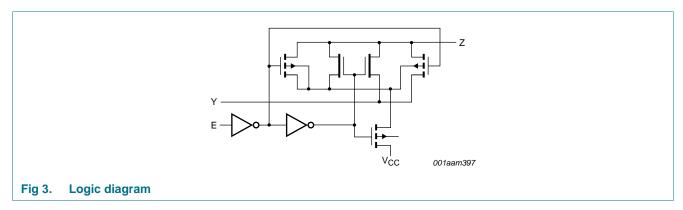
#### Table 2. Marking

9	
Type number	Marking code <sup>[1]</sup>
74LVC1G66GW	VL
74LVC1G66GV	V66
74LVC1G66GM	VL
74LVC1G66GF	VL
74LVC1G66GN	VL
74LVC1G66GS	VL

<sup>[1]</sup> The pin 1 indicator is located on the lower left corner of the device, below the marking code.

# 5. Functional diagram

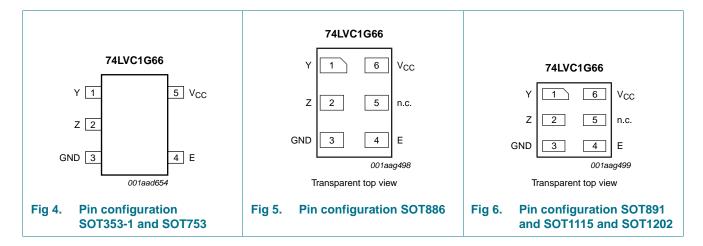




**Bilateral** switch

# 6. Pinning information

### 6.1 Pinning



### 6.2 Pin description

Table 3. Pin description

Symbol	Pin		Description
	SOT353-1, SOT753	SOT886, SOT891, SOT1115 and SOT1202	
Υ	1	1	independent input or output
Z	2	2	independent output or input
GND	3	3	ground (0 V)
Е	4	4	enable input (active HIGH)
n.c.	-	5	not connected
V <sub>CC</sub>	5	6	supply voltage

# 7. Functional description

Table 4. Function table[1]

Input E	Switch
L	OFF-state
Н	ON-state

[1] H = HIGH voltage level; L = LOW voltage level

## 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC}$	supply voltage		-0.5	+6.5	V
VI	input voltage		<u>[1]</u> –0.5	+6.5	V
I <sub>IK</sub>	input clamping current	$V_I < -0.5 \text{ V or } V_I > V_{CC} + 0.5 \text{ V}$	-50	-	mA
I <sub>SK</sub>	switch clamping current	$V_I < -0.5 \text{ V or } V_I > V_{CC} + 0.5 \text{ V}$	-	±50	mA
V <sub>SW</sub>	switch voltage	enable and disable mode	[2] -0.5	$V_{CC} + 0.5$	V
I <sub>SW</sub>	switch current	$V_{SW} > -0.5 \text{ V or } V_{SW} < V_{CC} + 0.5 \text{ V}$	-	±50	mA
I <sub>CC</sub>	supply current		-	100	mA
$I_{GND}$	ground current		-100	-	mA
T <sub>stg</sub>	storage temperature		-65	+150	°C
P <sub>tot</sub>	total power dissipation	$T_{amb} = -40 ^{\circ}$ C to +125 $^{\circ}$ C	[3]	250	mW

<sup>[1]</sup> The minimum input voltage rating may be exceeded if the input current rating is observed.

# 9. Recommended operating conditions

Table 6. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{CC}$	supply voltage		1.65	-	5.5	V
VI	input voltage		0	-	5.5	V
V <sub>SW</sub>	switch voltage		<u>[1]</u> 0	-	$V_{CC}$	V
T <sub>amb</sub>	ambient temperature		-40	-	+125	°C
Δt/ΔV	input transition rise and	$V_{CC} = 1.65 \text{ V to } 2.7 \text{ V}$	[2] -	-	20	ns/V
	fall rate	$V_{CC} = 2.7 \text{ V to } 5.5 \text{ V}$	[2] -	-	10	ns/V

<sup>[1]</sup> To avoid sinking GND current from terminal Z when switch current flows in terminal Y, the voltage drop across the bidirectional switch must not exceed 0.4 V. If the switch current flows into terminal Z, no GND current will flow from terminal Y. In this case, there is no limit for the voltage drop across the switch.

<sup>[2]</sup> The minimum and maximum switch voltage ratings may be exceeded if the switch clamping current rating is observed.

<sup>[3]</sup> For TSSOP5 and SC-74A packages: above 87.5 °C the value of P<sub>tot</sub> derates linearly with 4.0 mW/K. For XSON6 packages: above 118 °C the value of P<sub>tot</sub> derates linearly with 7.8 mW/K.

<sup>[2]</sup> Applies to control signal levels.

## 10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

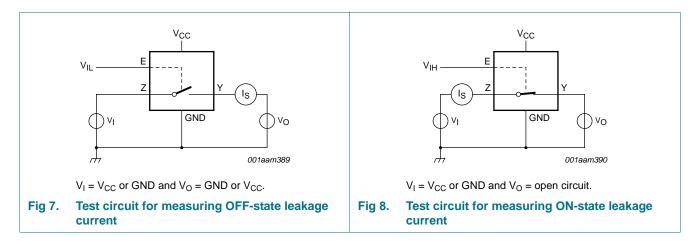
Symbol	Parameter	Conditions		-40 °	°C to +8	5 °C	-40 °C to	Unit	
				Min	Typ[1]	Max	Min	Max	
$V_{IH}$	HIGH-level	V <sub>CC</sub> = 1.65 V to 1.95 V		0.65V <sub>CC</sub>	-	-	0.65V <sub>CC</sub>	-	V
	input voltage	V <sub>CC</sub> = 2.3 V to 2.7 V		1.7	-	-	1.7	-	V
		V <sub>CC</sub> = 2.7 V to 3.6 V		2.0	-	-	2.0	-	V
		V <sub>CC</sub> = 4.5 V to 5.5 V		$0.7V_{CC}$	-	-	$0.7V_{CC}$	-	V
$V_{IL}$	LOW-level	V <sub>CC</sub> = 1.65 V to 1.95 V		-	-	0.35V <sub>CC</sub>	-	$0.35V_{CC}$	V
	input voltage	V <sub>CC</sub> = 2.3 V to 2.7 V		-	-	0.7	-	0.7	V
	V <sub>CC</sub> = 2.7 V to 3.6 V		-	-	0.8	-	0.8	V	
		V <sub>CC</sub> = 4.5 V to 5.5 V		-	-	$0.3V_{CC}$	-	$0.3V_{CC}$	V
II	input leakage current	pin E; $V_I = 5.5 \text{ V or GND}$ ; $V_{CC} = 0 \text{ V to } 5.5 \text{ V}$	[2]	-	±0.1	±5	-	±100	μΑ
I <sub>S(OFF)</sub>	OFF-state leakage current	V <sub>CC</sub> = 5.5 V; see <u>Figure 7</u>	[2]	-	±0.1	±5	-	±200	μΑ
I <sub>S(ON)</sub>	ON-state leakage current	V <sub>CC</sub> = 5.5 V; see <u>Figure 8</u>	[2]	-	±0.1	±5	-	±200	μΑ
I <sub>CC</sub>	supply current	$V_I$ = 5.5 V or GND; $V_{SW}$ = GND or $V_{CC}$ ; $V_{CC}$ = 1.65 V to 5.5 V	[2]	-	0.1	10	-	200	μА
$\Delta I_{CC}$	additional supply current	pin E; $V_I = V_{CC} - 0.6 \text{ V}$ ; $V_{SW} = \text{GND or } V_{CC}$ ; $V_{CC} = 5.5 \text{ V}$	[2]	-	5	500	-	5000	μΑ
C <sub>I</sub>	input capacitance			-	2.0	-	-	-	pF
$C_{S(OFF)}$	OFF-state capacitance			-	6.5	-	-	-	pF
C <sub>S(ON)</sub>	ON-state capacitance			-	11	-	-	-	pF

<sup>[1]</sup> All typical values are measured at  $T_{amb}$  = 25 °C.

<sup>[2]</sup> These typical values are measured at  $V_{CC}$  = 3.3 V.

**Bilateral** switch

### 10.1 Test circuits



### 10.2 ON resistance

Table 8. ON resistance

At recommended operating conditions; voltages are referenced to GND (ground 0 V); for graphs see Figure 10 to Figure 15.

Symbol	Parameter	Conditions	-40	°C to +8	35 °C	-40 °C to +125 °C		Unit
				Typ[1]	Max	Min	Max	
R <sub>ON(peak)</sub>	ON resistance (peak)	$V_I = GND$ to $V_{CC}$ ; see Figure 9						
		$I_{SW} = 4 \text{ mA};$ $V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	-	34.0	130	-	195	Ω
		$I_{SW}$ = 8 mA; $V_{CC}$ = 2.3 V to 2.7 V	-	12.0	30	-	45	Ω
		$I_{SW}$ = 12 mA; $V_{CC}$ = 2.7 V	-	10.4	25	-	38	Ω
		$I_{SW}$ = 24 mA; $V_{CC}$ = 3.0 V to 3.6 V	-	7.8	20	-	30	Ω
		$I_{SW}$ = 32 mA; $V_{CC}$ = 4.5 V to 5.5 V	-	6.2	15	-	23	Ω
$R_{ON(rail)}$	ON resistance (rail)	V <sub>I</sub> = GND; see <u>Figure 9</u>						
		$I_{SW} = 4 \text{ mA};$ $V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	-	8.2	18	-	27	Ω
		$I_{SW}$ = 8 mA; $V_{CC}$ = 2.3 V to 2.7 V	-	7.1	16	-	24	Ω
		$I_{SW} = 12 \text{ mA}; V_{CC} = 2.7 \text{ V}$	-	6.9	14	-	21	Ω
		$I_{SW}$ = 24 mA; $V_{CC}$ = 3.0 V to 3.6 V	-	6.5	12	-	18	Ω
		$I_{SW}$ = 32 mA; $V_{CC}$ = 4.5 V to 5.5 V	-	5.8	10	-	15	Ω
		V <sub>I</sub> = V <sub>CC</sub> ; see <u>Figure 9</u>						
		$I_{SW} = 4 \text{ mA};$ $V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	-	10.4	30	-	45	Ω
		$I_{SW}$ = 8 mA; $V_{CC}$ = 2.3 V to 2.7 V	-	7.6	20	-	30	Ω
		$I_{SW} = 12 \text{ mA}; V_{CC} = 2.7 \text{ V}$	-	7.0	18	-	27	Ω
		$I_{SW}$ = 24 mA; $V_{CC}$ = 3.0 V to 3.6 V	-	6.1	15	-	23	Ω
		$I_{SW}$ = 32 mA; $V_{CC}$ = 4.5 V to 5.5 V	-	4.9	10	-	15	Ω

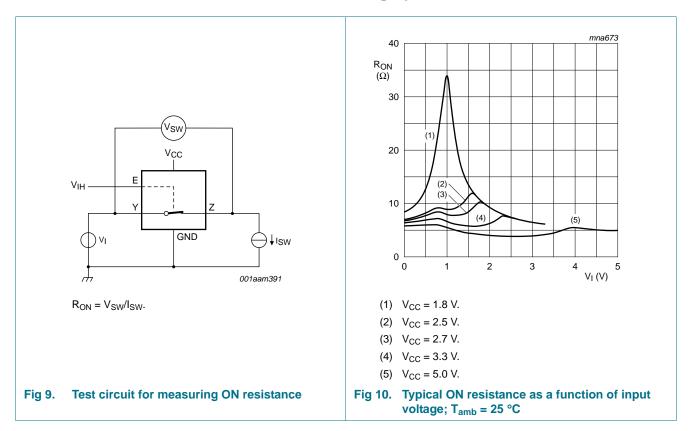
Table 8. ON resistance ... continued

At recommended operating conditions; voltages are referenced to GND (ground 0 V); for graphs see Figure 10 to Figure 15.

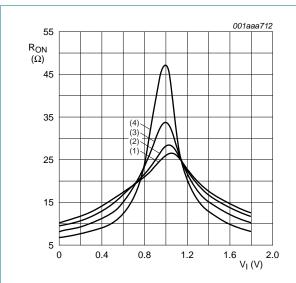
Symbol	Parameter	Conditions			-40 °C to +85 °C			-40 °C to +125 °C		
				Min	Typ[1]	Max	Min	Max		
R <sub>ON(flat)</sub>	ON resistance	$V_I = GND$ to $V_{CC}$	[2]							
	(flatness)	$I_{SW} = 4 \text{ mA};$ $V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		-	26.0	-	-	-	Ω	
		$I_{SW}$ = 8 mA; $V_{CC}$ = 2.3 V to 2.7 V		-	5.0	-	-	-	Ω	
		$I_{SW} = 12 \text{ mA}; V_{CC} = 2.7 \text{ V}$		-	3.5	-	-	-	Ω	
		$I_{SW}$ = 24 mA; $V_{CC}$ = 3.0 V to 3.6 V		-	2.0	-	-	-	Ω	
		$I_{SW}$ = 32 mA; $V_{CC}$ = 4.5 V to 5.5 V		-	1.5	-	-	-	Ω	

<sup>[1]</sup> Typical values are measured at  $T_{amb}$  = 25 °C and nominal  $V_{CC}$ .

### 10.3 ON resistance test circuit and graphs



<sup>[2]</sup> Flatness is defined as the difference between the maximum and minimum value of ON resistance measured at identical V<sub>CC</sub> and temperature.

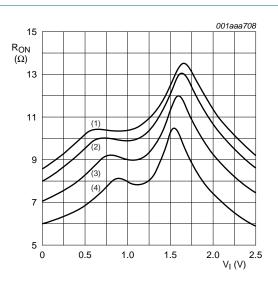


(1)  $T_{amb} = 125 \, ^{\circ}C$ .

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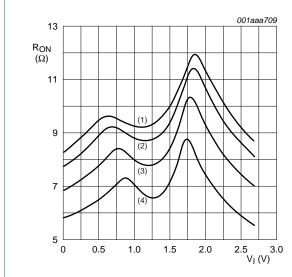
- (2)  $T_{amb} = 85 \, ^{\circ}C$ .
- (3)  $T_{amb} = 25 \, ^{\circ}C$ .
- (4)  $T_{amb} = -40 \, ^{\circ}C$ .

Fig 11. ON resistance as a function of input voltage;  $V_{CC} = 1.8 \text{ V}$ 



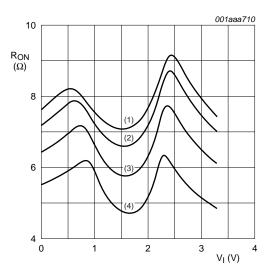
- (1)  $T_{amb} = 125 \, ^{\circ}C$ .
- (2)  $T_{amb} = 85 \, ^{\circ}C$ .
- (3)  $T_{amb} = 25 \, ^{\circ}C$ .
- (4)  $T_{amb} = -40 \, ^{\circ}C$ .

Fig 12. ON resistance as a function of input voltage;  $V_{CC} = 2.5 \text{ V}$ 



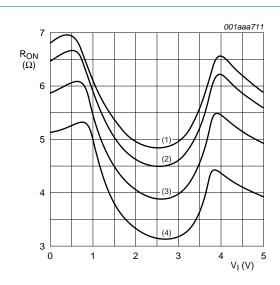
- (1)  $T_{amb} = 125 \, ^{\circ}C$ .
- (2)  $T_{amb} = 85 \, ^{\circ}C$ .
- (3)  $T_{amb} = 25 \, ^{\circ}C$ .
- (4)  $T_{amb} = -40 \, ^{\circ}C$ .

Fig 13. ON resistance as a function of input voltage;  $V_{CC} = 2.7 \text{ V}$ 



- (1)  $T_{amb} = 125 \, ^{\circ}C$ .
- (2)  $T_{amb} = 85 \, ^{\circ}C$ .
- (3)  $T_{amb} = 25 \, ^{\circ}C$ .
- (4)  $T_{amb} = -40 \, ^{\circ}C$ .

Fig 14. ON resistance as a function of input voltage;  $V_{CC} = 3.3 \text{ V}$ 



- (1)  $T_{amb} = 125 \, ^{\circ}C$ .
- (2)  $T_{amb} = 85 \, ^{\circ}C$ .
- (3)  $T_{amb} = 25 \, ^{\circ}C$ .
- (4)  $T_{amb} = -40 \, ^{\circ}C$ .

Fig 15. ON resistance as a function of input voltage;  $V_{CC} = 5.0 \text{ V}$ 

# 11. Dynamic characteristics

Table 9. Dynamic characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V); for test circuit see Figure 18.

Symbol	Parameter	Conditions		-40	°C to +8	5 °C	-40 °C to	Unit	
				Min	Typ[1]	Max	Min	Max	
t <sub>pd</sub>	propagation delay	Y to Z or Z to Y; see Figure 16	[2][3]						
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		-	0.8	2.0	-	3.0	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		-	0.4	1.2	-	2.0	ns
		V <sub>CC</sub> = 2.7 V		-	0.4	1.0	-	1.5	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		-	0.3	0.8	-	1.5	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$		-	0.2	0.6	-	1.0	ns
t <sub>en</sub>	enable time	E to Y or Z; see Figure 17	<u>[4]</u>						
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		1.0	5.3	12	1.0	15.5	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		1.0	3.0	6.5	1.0	8.5	ns
		$V_{CC} = 2.7 \text{ V}$		1.0	2.6	6.0	1.0	8.0	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		1.0	2.5	5.0	1.0	6.5	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$		1.0	1.9	4.2	1.0	5.5	ns

**Dynamic characteristics** ...continued Table 9.

At recommended operating conditions; voltages are referenced to GND (ground = 0 V); for test circuit see Figure 18.

Symbol	Parameter	Conditions		-40 °C to +85 °C			-40 °C to	+125 °C	Unit
				Min	Typ[1]	Max	Min	Max	
t <sub>dis</sub>	disable time	E to Y or Z; see Figure 17	[5]				•		•
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		1.0	4.2	10	1.0	13	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		1.0	2.4	6.9	1.0	9.0	ns
		$V_{CC} = 2.7 \text{ V}$		1.0	3.6	7.5	1.0	9.5	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		1.0	3.4	6.5	1.0	8.5	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$		1.0	2.5	5.0	1.0	6.5	ns
$C_{PD}$	power dissipation capacitance	$C_L = 50 \text{ pF}; f_i = 10 \text{ MHz};$ $V_I = \text{GND to } V_{CC}$	[6]						
		$V_{CC} = 2.5 \text{ V}$		-	9.8	-	-	-	pF
		$V_{CC} = 3.3 \text{ V}$		-	12.0	-	-	-	pF
		$V_{CC} = 5.0 \text{ V}$		-	17.3	-	-	-	pF

- [1] Typical values are measured at  $T_{amb}$  = 25 °C and nominal  $V_{CC}$ .
- [2]  $t_{pd}$  is the same as  $t_{PLH}$  and  $t_{PHL}$
- propagation delay is the calculated RC time constant of the typical ON resistance of the switch and the specified capacitance when driven by an ideal voltage source (zero output impedance).
- [4] ten is the same as tPZH and tPZL
- [5] t<sub>dis</sub> is the same as t<sub>PLZ</sub> and t<sub>PHZ</sub>
- [6]  $C_{PD}$  is used to determine the dynamic power dissipation ( $P_D$  in  $\mu W$ ).

 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma \{ (C_L + C_{S(ON)}) \times V_{CC}^2 \times f_o \} \text{ where: }$ 

f<sub>i</sub> = input frequency in MHz;

f<sub>o</sub> = output frequency in MHz;

C<sub>L</sub> = output load capacitance in pF;

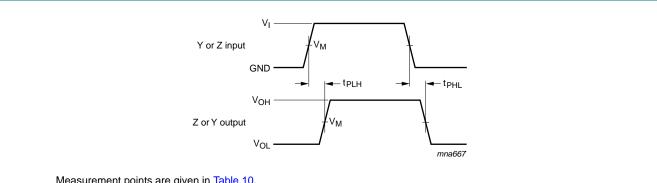
C<sub>S(ON)</sub> = maximum ON-state switch capacitance in pF;

V<sub>CC</sub> = supply voltage in V;

N = number of inputs switching;

 $\Sigma \{(C_L + C_{S(ON)}) \times V_{CC}^2 \times f_o\} = \text{sum of the outputs.}$ 

#### 11.1 Waveforms and test circuit



Measurement points are given in Table 10.

Logic levels:  $V_{OL}$  and  $V_{OH}$  are typical output voltage levels that occur with the output load.

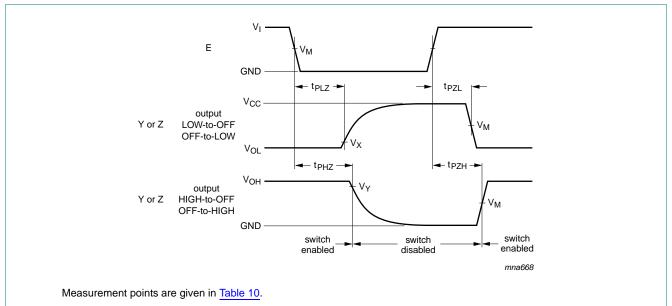
Fig 16. Input (Y or Z) to output (Z or Y) propagation delays

74LVC1G66

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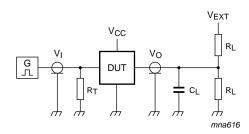


Logic levels:  $V_{\text{OL}}$  and  $V_{\text{OH}}$  are typical output voltage levels that occur with the output load.

Fig 17. Enable and disable times

Table 10. Measurement points

Supply voltage	Input	Output		
V <sub>CC</sub>	V <sub>M</sub>	V <sub>M</sub>	V <sub>X</sub>	V <sub>Y</sub>
1.65 V to 1.95 V	0.5V <sub>CC</sub>	0.5V <sub>CC</sub>	V <sub>OL</sub> + 0.15 V	V <sub>OH</sub> – 0.15 V
2.3 V to 2.7 V	0.5V <sub>CC</sub>	0.5V <sub>CC</sub>	V <sub>OL</sub> + 0.15 V	V <sub>OH</sub> – 0.15 V
2.7 V	1.5 V	1.5 V	V <sub>OL</sub> + 0.3 V	$V_{OH} - 0.3 V$
3.0 V to 3.6 V	1.5 V	1.5 V	V <sub>OL</sub> + 0.3 V	$V_{OH} - 0.3 V$
4.5 V to 5.5 V	0.5V <sub>CC</sub>	0.5V <sub>CC</sub>	V <sub>OL</sub> + 0.3 V	$V_{OH} - 0.3 V$



Test data is given in Table 11.

Definitions for test circuit:

 $R_T$  = Termination resistance should be equal to output impedance  $Z_o$  of the pulse generator.

C<sub>L</sub> = Load capacitance including jig and probe capacitance.

R<sub>L</sub> = Load resistance.

 $V_{\text{EXT}}$  = External voltage for measuring switching times.

Fig 18. Test circuit for measuring switching times

Table 11. Test data

Supply voltage Input		Load	Load		V <sub>EXT</sub>			
V <sub>CC</sub>	VI	t <sub>r</sub> , t <sub>f</sub>	CL	R <sub>L</sub>	t <sub>PLH</sub> , t <sub>PHL</sub>	t <sub>PZH</sub> , t <sub>PHZ</sub>	t <sub>PZL</sub> , t <sub>PLZ</sub>	
1.65 V to 1.95 V	$V_{CC}$	$\leq$ 2.0 ns	30 pF	1 k $\Omega$	open	GND	2V <sub>CC</sub>	
2.3 V to 2.7 V	$V_{CC}$	≤ 2.0 ns	30 pF	$500 \Omega$	open	GND	2V <sub>CC</sub>	
2.7 V	2.7 V	≤ 2.5 ns	50 pF	$500 \Omega$	open	GND	6 V	
3.0 V to 3.6 V	2.7 V	≤ 2.5 ns	50 pF	$500 \Omega$	open	GND	6 V	
4.5 V to 5.5 V	V <sub>CC</sub>	≤ 2.5 ns	50 pF	$500\Omega$	open	GND	2V <sub>CC</sub>	

### 11.2 Additional dynamic characteristics

Table 12. Additional dynamic characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V); T<sub>amb</sub> = 25 °C.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
THD	total harmonic distortion	$R_L = 10 \text{ k}\Omega; C_L = 50 \text{ pF}; f_i = 1 \text{ kHz};$ see Figure 19				
		V <sub>CC</sub> = 1.65 V	-	0.032	-	%
		V <sub>CC</sub> = 2.3 V	-	0.008	-	%
		$V_{CC} = 3.0 \text{ V}$	-	0.006	-	%
		V <sub>CC</sub> = 4.5 V	-	0.001	-	%
		$R_L$ = 10 k $\Omega$ ; $C_L$ = 50 pF; $f_i$ = 10 kHz; see Figure 19				
		V <sub>CC</sub> = 1.65 V	-	0.068	-	%
		V <sub>CC</sub> = 2.3 V	-	0.009	-	%
		V <sub>CC</sub> = 3.0 V	-	0.008	-	%
		V <sub>CC</sub> = 4.5 V	-	0.006	-	%

NXP Semiconductors 74LVC1G66

**Bilateral switch** 

 Table 12.
 Additional dynamic characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V); T<sub>amb</sub> = 25 °C.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
(-3dB)	-3 dB frequency response	$R_L = 600 \Omega$ ; $C_L = 50 pF$ ; see <u>Figure 20</u>				
		V <sub>CC</sub> = 1.65 V	-	135	-	MHz
		$V_{CC} = 2.3 \text{ V}$	-	145	-	MHz
		$V_{CC} = 3.0 \text{ V}$	-	150	-	MHz
		$V_{CC} = 4.5 \text{ V}$	-	155	-	MHz
		$R_L = 50 \Omega$ ; $C_L = 5 pF$ ; see Figure 20				
		V <sub>CC</sub> = 1.65 V	-	> 500	-	MHz
		$V_{CC} = 2.3 \text{ V}$	-	> 500	-	MHz
		$V_{CC} = 3.0 \text{ V}$	-	> 500	-	MHz
		$V_{CC} = 4.5 \text{ V}$	-	> 500	-	MHz
		$R_L = 50 \Omega$ ; $C_L = 10 pF$ ; see Figure 20				
		V <sub>CC</sub> = 1.65 V	-	200	-	MHz
		$V_{CC} = 2.3 \text{ V}$	-	350	-	MHz
		$V_{CC} = 3.0 \text{ V}$	-	410	-	MHz
		V <sub>CC</sub> = 4.5 V	-	440	-	MHz
$\iota_{iso}$	isolation (OFF-state)	$R_L = 600 \Omega$ ; $C_L = 50 pF$ ; $f_i = 1 MHz$ ; see Figure 21				
		V <sub>CC</sub> = 1.65 V	-	-46	-	dB
		$V_{CC} = 2.3 \text{ V}$	-	-46	-	dB
		V <sub>CC</sub> = 3.0 V	-	-46	-	dB
		V <sub>CC</sub> = 4.5 V	-	-46	-	dB
		$R_L = 50 \Omega$ ; $C_L = 5 pF$ ; $f_i = 1 MHz$ ; see Figure 21				
		V <sub>CC</sub> = 1.65 V	-	-37	-	dB
		V <sub>CC</sub> = 2.3 V	-	-37	-	dB
		V <sub>CC</sub> = 3.0 V	-	-37	-	dB
		V <sub>CC</sub> = 4.5 V	-	-37	-	dB
V <sub>ct</sub>	crosstalk voltage	between digital input and switch; $R_L = 600 \Omega$ ; $C_L = 50 pF$ ; $f_i = 1 MHz$ ; $t_r = t_f = 2 ns$ ; see Figure 22				
		V <sub>CC</sub> = 1.65 V	-	69	-	mV
		V <sub>CC</sub> = 2.3 V	-	87	-	mV
		V <sub>CC</sub> = 3.0 V	-	156	-	mV
		V <sub>CC</sub> = 4.5 V	-	302	-	mV

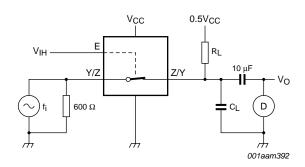
**Bilateral** switch

 Table 12.
 Additional dynamic characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V); T<sub>amb</sub> = 25 °C.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$Q_{inj}$	charge injection	$C_L$ = 0.1 nF; $V_{gen}$ = 0 V; $R_{gen}$ = 0 $\Omega$ ; $f_i$ = 1 MHz; $R_L$ = 1 M $\Omega$ ; see <u>Figure 23</u>				
		V <sub>CC</sub> = 1.8 V	-	3.3	-	рC
		V <sub>CC</sub> = 2.5 V	-	4.1	-	рС
		V <sub>CC</sub> = 3.3 V	-	5.0	-	рС
		V <sub>CC</sub> = 4.5 V	-	6.4	-	рС
		V <sub>CC</sub> = 5.5 V	-	7.5	-	рC

### 11.3 Test circuits



#### Test conditions:

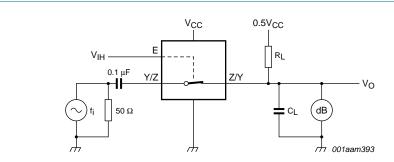
 $V_{CC} = 1.65 \text{ V: } V_i = 1.4 \text{ V (p-p)}.$ 

 $V_{CC} = 2.3 \text{ V: } V_i = 2 \text{ V (p-p)}.$ 

 $V_{CC} = 3 \text{ V: } V_i = 2.5 \text{ V (p-p)}.$ 

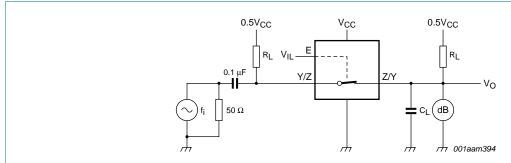
 $V_{CC} = 4.5 \text{ V: } V_i = 4 \text{ V (p-p)}.$ 

Fig 19. Test circuit for measuring total harmonic distortion



 $\label{eq:definition} \mbox{Adjust} \ f_i \ \mbox{voltage to obtain 0 dBm level at output. Increase} \ f_i \ \mbox{frequency until dB meter reads} \ -3 \ \mbox{dB}.$ 

Fig 20. Test circuit for measuring the frequency response when switch is in ON-state



Adjust fi voltage to obtain 0 dBm level at input.

Fig 21. Test circuit for measuring isolation (OFF-state)

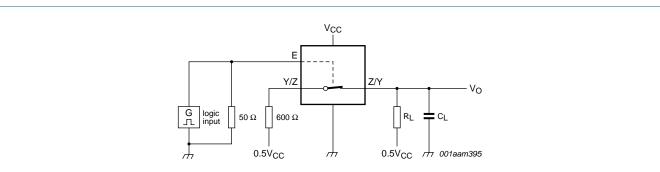
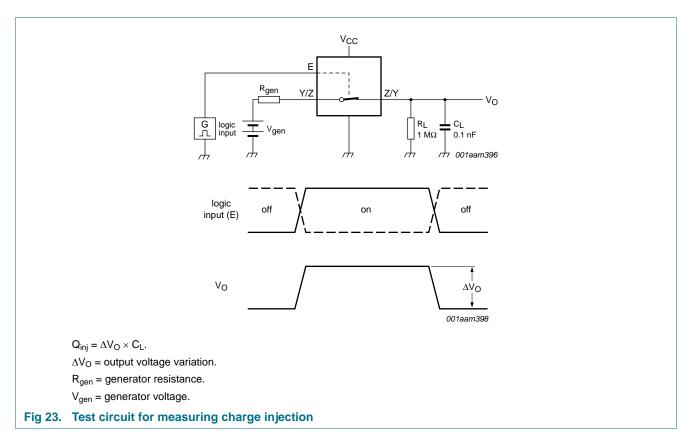


Fig 22. Test circuit for measuring crosstalk between digital input and switch

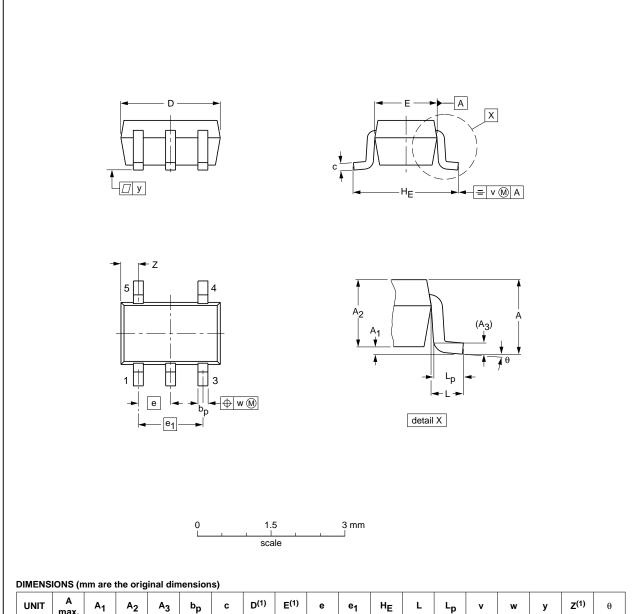


74LVC1G66

# 12. Package outline

### TSSOP5: plastic thin shrink small outline package; 5 leads; body width 1.25 mm

SOT353-1



UNIT	A max.	A <sub>1</sub>	A <sub>2</sub>	A <sub>3</sub>	bp	C	D <sup>(1)</sup>	E <sup>(1)</sup>	e	e <sub>1</sub>	HE	L	L <sub>p</sub>	v	w	у	Z <sup>(1)</sup>	θ
mm	1.1	0.1 0	1.0 0.8	0.15	0.30 0.15	0.25 0.08	2.25 1.85	1.35 1.15	0.65	1.3	2.25 2.0	0.425	0.46 0.21	0.3	0.1	0.1	0.60 0.15	7° 0°

#### Note

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT353-1		MO-203	SC-88A			<del>-00-09-01</del> 03-02-19

Fig 24. Package outline SOT353-1 (TSSOP5)

74LVC1G66

#### Plastic surface-mounted package; 5 leads

**SOT753** 

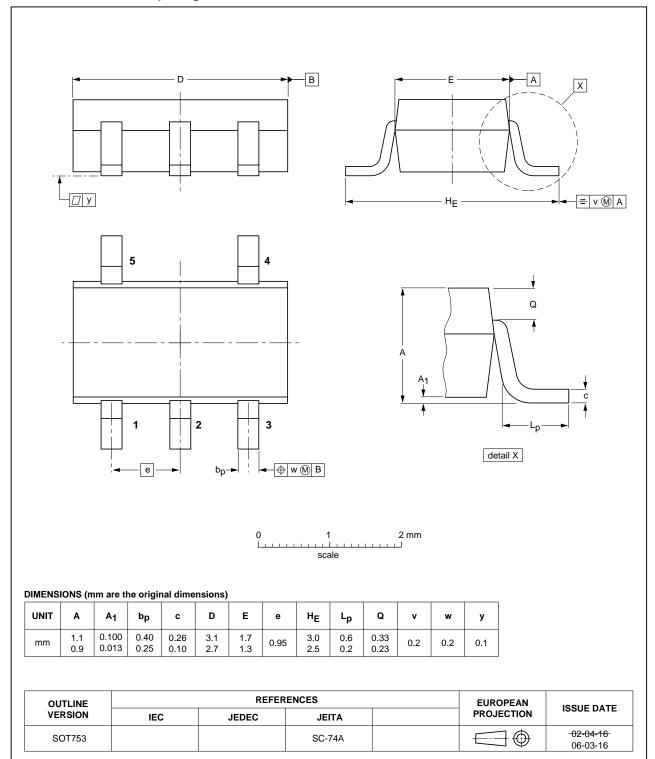


Fig 25. Package outline SOT753 (SC-74A)

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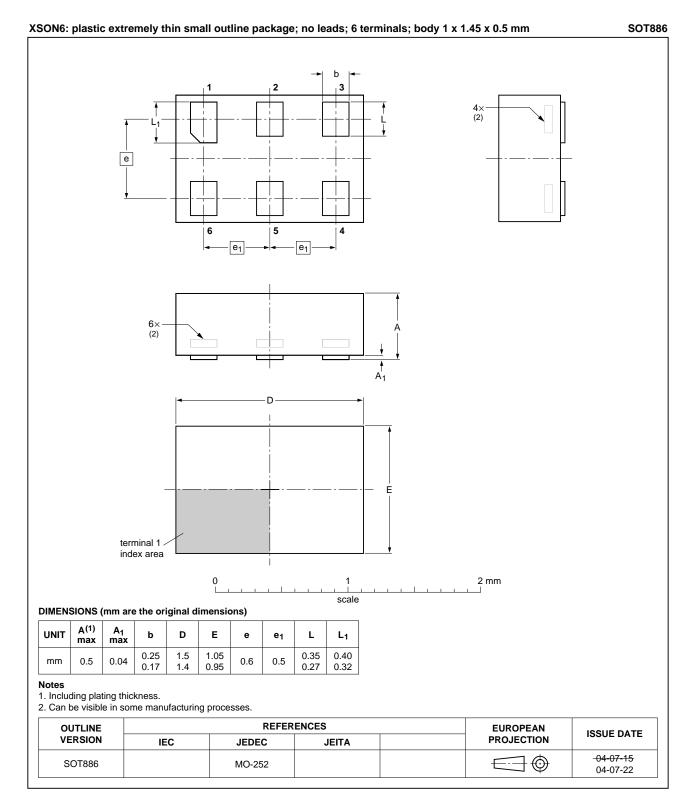


Fig 26. Package outline SOT886 (XSON6)

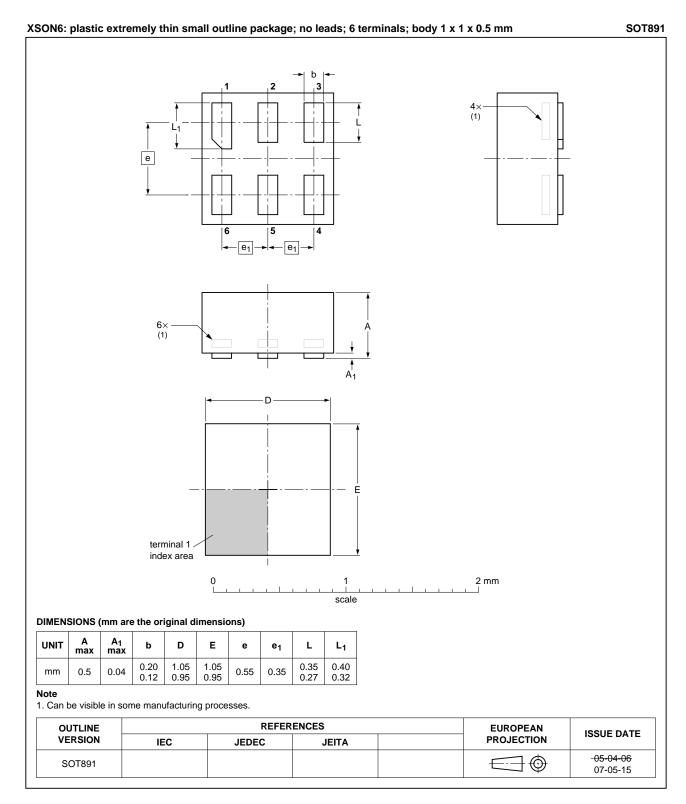


Fig 27. Package outline SOT891 (XSON6)

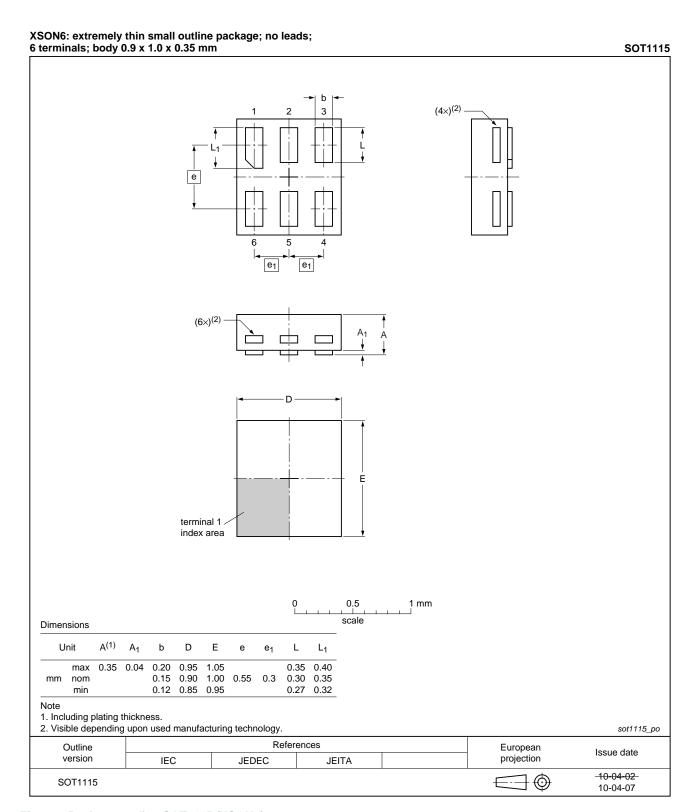


Fig 28. Package outline SOT1115 (XSON6)

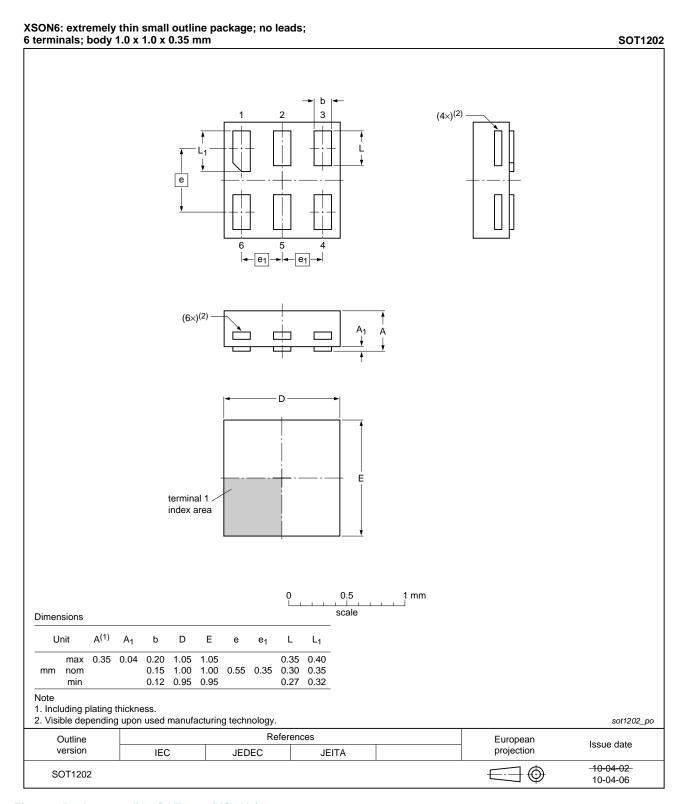


Fig 29. Package outline SOT1202 (XSON6)

**Bilateral switch** 

## 13. Abbreviations

#### Table 13. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
TTL	Transistor-Transistor Logic
HBM	Human Body Model
ESD	ElectroStatic Discharge
MM	Machine Model
DUT	Device Under Test

# 14. Revision history

### Table 14. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74LVC1G66 v.8	20111202	Product data sheet	-	74LVC1G66 v.7
Modifications:	<ul> <li>Legal pages</li> </ul>	s updated.		
74LVC1G66 v.7	20100730	Product data sheet	-	74LVC1G66 v.6
74LVC1G66 v.6	20070827	Product data sheet	-	74LVC1G66 v.5
74LVC1G66 v.5	20070807	Product data sheet	-	74LVC1G66 v.4
74LVC1G66 v.4	20040413	Product specification	-	74LVC1G66 v.3
74LVC1G66 v.3	20021115	Product specification	-	74LVC1G66 v.2
74LVC1G66 v.2	20020529	Product specification	-	74LVC1G66 v.1
74LVC1G66 v.1	20011030	Product specification	-	-

### 15. Legal information

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Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions"
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### 17. Contents

1	General description
2	Features and benefits
3	Ordering information 1
4	Marking 2
5	Functional diagram 2
6	Pinning information
6.1	Pinning
6.2	Pin description
7	Functional description 3
8	Limiting values 4
9	Recommended operating conditions 4
10	Static characteristics 5
10.1	Test circuits 6
10.2	ON resistance
10.3	ON resistance test circuit and graphs 7
11	Dynamic characteristics 9
11.1	Waveforms and test circuit 10
11.2	Additional dynamic characteristics 12
11.3	Test circuits
12	Package outline
13	Abbreviations
14	Revision history
15	Legal information
15.1	Data sheet status 23
15.2	Definitions
15.3	Disclaimers
15.4	Trademarks24
16	Contact information 24
17	Contents

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